

## 1. General description

Silicon Carbide MOSFET in a TSPAK plastic package with top side cooling structure, designed for high frequency, high efficiency systems.



## 2. Features and benefits

- Top side cooling structure
- Kelvin source configuration
- Low specific on-resistance
- Optimized dynamic performance
- Robust gate design
- 0V turn-off  $V_{GS}$  for simple gate driver
- 100% UIS Tested
- Easy to parallel
- RoHS compliant



## 3. Applications

- Switching mode power supplies
- UPS and energy storage systems
- Battery formation instrument
- PV MPPT and inverters
- EV Chargers
- Welding machines
- Motor Drives

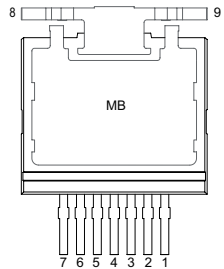
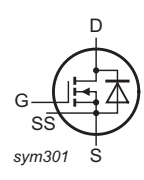
## 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Notes	Values			Unit
<b>Absolute maximum rating</b>							
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		1200			V
$I_D$	drain current	$V_{GS} = 18\text{ V}; T_{mb} = 25\text{ °C}$		210			A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}, T_j = 175\text{ °C}$		1012			W
$T_j$	junction temperature			-55 to 175			°C
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 15\text{ V}; I_D = 75\text{ A}; T_j = 25\text{ °C}$		-	12	-	mΩ
		$V_{GS} = 18\text{ V}; I_D = 75\text{ A}; T_j = 25\text{ °C}$		-	9.8	25	mΩ
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 75\text{ A}; V_{DS} = 800\text{ V}; V_{GS} = -4\text{ V}/18\text{ V}; T_j = 25\text{ °C}$		-	321	-	nC
$Q_{GD}$	gate-drain charge			-	57	-	nC
<b>Source-drain diode</b>							
$Q_r$	recovered charge	$I_{SD} = 50\text{ A}; di/dt = 500\text{ A}/\mu\text{s}; V_{DS} = 400\text{ V}; T_j = 25\text{ °C}$		-	250	-	nC

## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		 sym301
2	SS	source sense		
3-7	S	source		
8-9 mb	D	mounting base; connected to drain		

## 6. Ordering information

Table 3. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2M12120TB	TSPAK	WNSC2M12120TB6J	Reel	600	TSPAKH	06-Dec-2024

## 7. Marking

Table 4. Marking codes

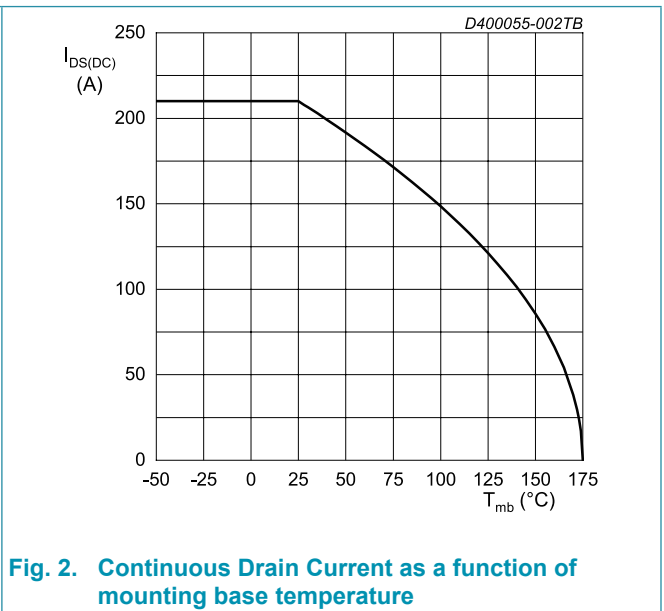
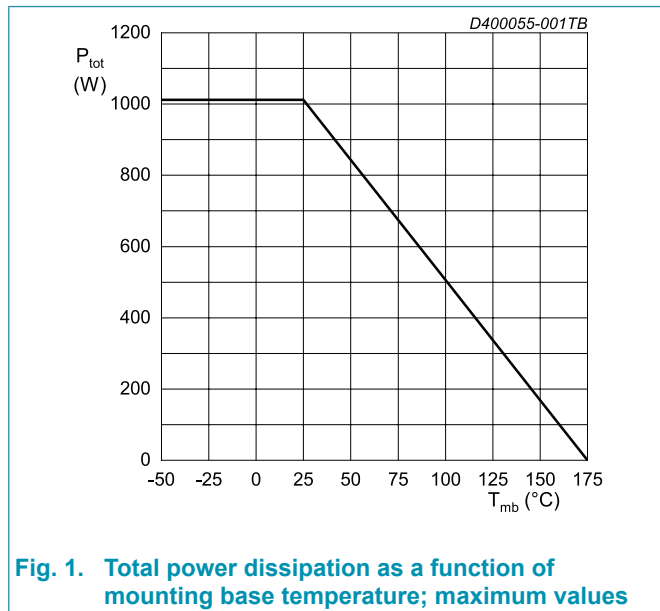
Type number	Marking codes
WNSC2M12120TB	WNSC2M 12120TB

## 8. Limiting values

**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Notes	Values	Unit
$V_{DS}$	drain-source voltage	$25\text{ °C} \leq T_j \leq 175\text{ °C}$		1200	V
$V_{GS,max}$	gate-source voltage			-12 to 24	V
$V_{GS,op}$	gate-source voltage			-4 to 18	V
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}, T_j = 175\text{ °C}$		1012	W
$I_D$	drain current	$V_{GS} = 18\text{ V}; T_{mb} = 25\text{ °C}$		210	A
		$V_{GS} = 18\text{ V}; T_{mb} = 100\text{ °C}$		149	A
$I_{DM}$	peak drain current	pulse width $t_p$ limited by $T_{j,max}$	Fig.17	420	A
$I_S$	continuous diode current	$V_{GS} = -4\text{ V}; T_{mb} = 25\text{ °C}$		142	A
$I_{SM}$	pulse diode current	$V_{GS} = -4\text{ V}$ ; pulse width $t_p$ limited by $T_{j,max}$		420	A
$E_{as}$	single pulse drain-to-source avalanche	$I_{AS} = 35\text{ A}; L = 1\text{ mH}; V_{DD} = 100\text{ V}; T_j = 25\text{ °C}$		613	mJ
$T_{stg}$	storage temperature			-55 to 175	°C
$T_j$	junction temperature			-55 to 175	°C
$T_{sld(M)}$	peak soldering temperature			245	°C



### 9. Thermal & Mechanical characteristics

Table 6. Thermal & Mechanical characteristics

Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base			-	0.15	-	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		-	40	-	K/W

Note: Device is ESD sensitive. Handling precautions are recommended.

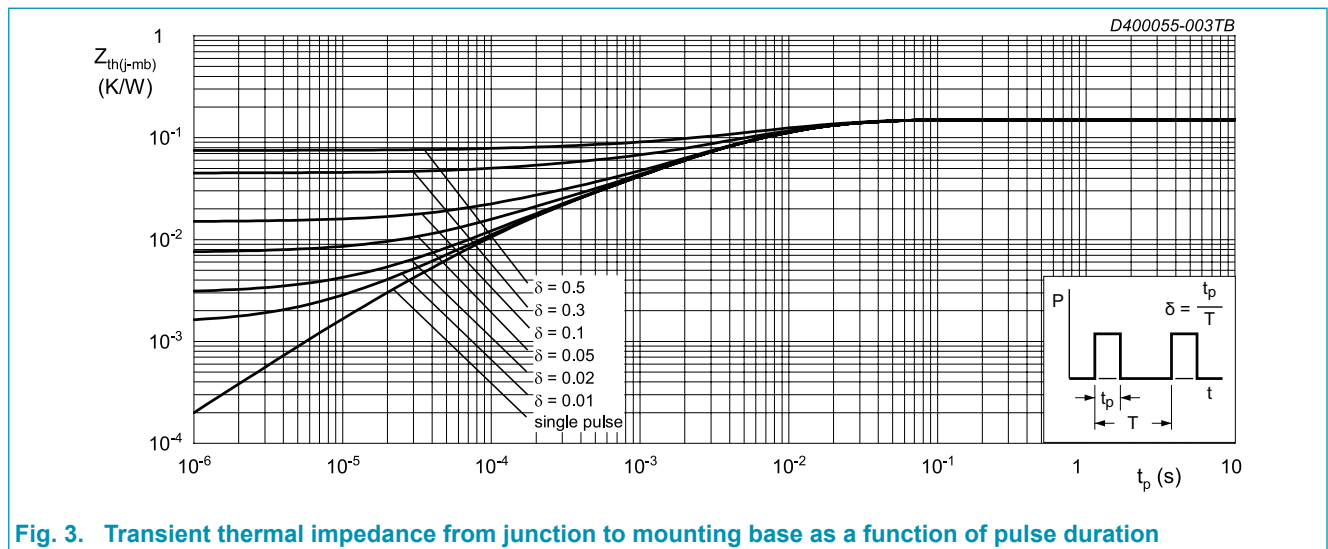
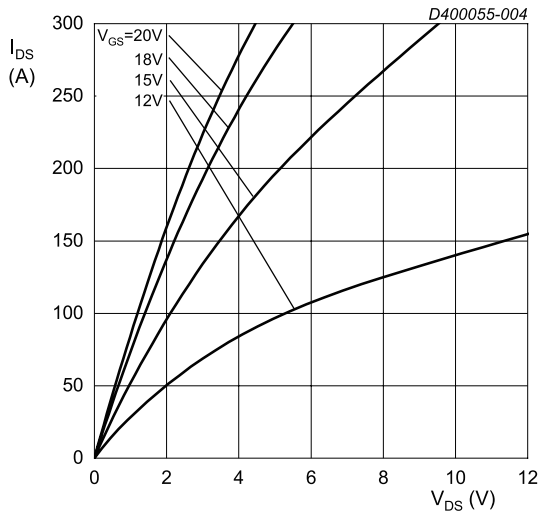


Fig. 3. Transient thermal impedance from junction to mounting base as a function of pulse duration

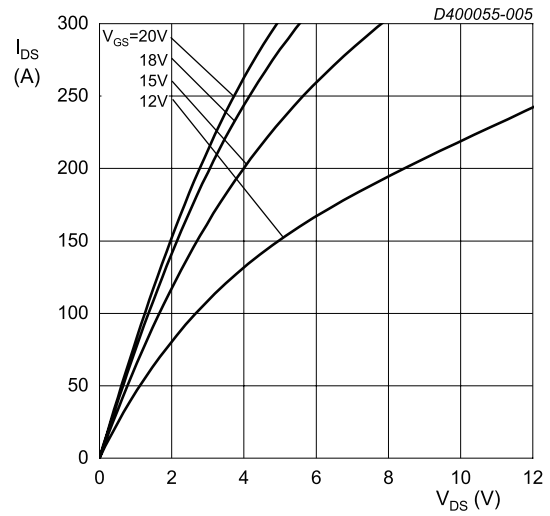
## 10. Characteristics

Table 7. Characteristics

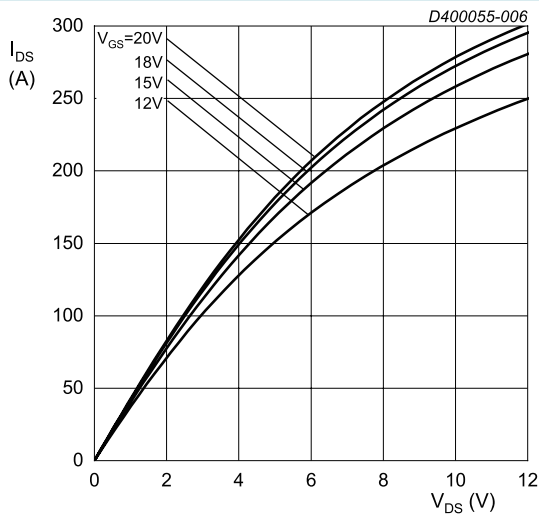
Symbol	Parameter	Conditions	Notes	Min	Typ	Max	Unit
<b>Static characteristics</b>							
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 100 \mu A; V_{GS} = 0 V; T_j = 25 \text{ }^\circ C$		1200	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 28 \text{ mA}; V_{DS} = 10 \text{ V}; T_j = 25 \text{ }^\circ C$		1.9	2.6	3.5	V
		$I_D = 28 \text{ mA}; V_{DS} = 10 \text{ V}; T_j = 175 \text{ }^\circ C$		-	1.9	-	V
$I_{DSS}$	drain leakage current	$V_{DS} = 1200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$		-	0.2	100	$\mu A$
		$V_{DS} = 1200 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ C$		-	2	-	$\mu A$
$I_{GSS}$	gate leakage current	$V_{GS} = 24 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$		-	10	100	nA
		$V_{GS} = -12 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ C$		-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 15 \text{ V}; I_D = 75 \text{ A}; T_j = 25 \text{ }^\circ C$		-	12	-	m $\Omega$
		$V_{GS} = 18 \text{ V}; I_D = 75 \text{ A}; T_j = 25 \text{ }^\circ C$		-	9.8	25	m $\Omega$
		$V_{GS} = 18 \text{ V}; I_D = 75 \text{ A}; T_j = 175 \text{ }^\circ C$		-	19.1	-	m $\Omega$
$R_G$	gate resistance	$f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$		-	0.53	-	$\Omega$
$g_{fs}$	transconductance	$V_{DS} = 20 \text{ V}; I_D = 75 \text{ A}; T_j = 25 \text{ }^\circ C$		-	56	-	S
<b>Dynamic characteristics</b>							
$Q_{G(tot)}$	total gate charge	$I_D = 75 \text{ A}; V_{DS} = 800 \text{ V}; V_{GS} = -4 \text{ V}/18 \text{ V}; T_j = 25 \text{ }^\circ C$		-	321	-	nC
$Q_{GS}$	gate-source charge			-	115	-	nC
$Q_{GD}$	gate-drain charge			-	57	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 1000 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25 \text{ }^\circ C$		-	6782	-	pF
$C_{oss}$	output capacitance			-	289	-	pF
$C_{rss}$	reverse transfer capacitance			-	23	-	pF
$E_{oss}$	Coss stored energy			-	145	-	$\mu J$
$t_{d(on)}$	turn-on delay time	$V_{DS} = 800 \text{ V}; V_{GS} = -4 \text{ V}/18 \text{ V}; R_{G(ext)} = 5.1 \Omega; I_D = 75 \text{ A}; L = 100 \mu H; T_j = 25 \text{ }^\circ C$		-	36	-	ns
$t_r$	rise time			-	65	-	ns
$t_{d(off)}$	turn-off delay time			-	86	-	ns
$t_f$	fall time			-	21	-	ns
$E_{on}$	turn-on energy (SiC Diode FWD)		Fig.20	-	1460	-	$\mu J$
$E_{off}$	turn-off energy (SiC Diode FWD)		Fig.20	-	1153	-	$\mu J$
$E_{on}$	turn-on energy (Body Diode FWD)		Fig.20	-	1833	-	$\mu J$
$E_{off}$	turn-off energy (Body Diode FWD)	Fig.20	-	1063	-	$\mu J$	
<b>Source-drain diode</b>							
$V_{SD}$	source-drain voltage	$V_{GS} = 0 \text{ V}; I_{SD} = 37.5 \text{ A}; T_j = 25 \text{ }^\circ C$		-	2.9	-	V
		$V_{GS} = -4 \text{ V}; I_{SD} = 37.5 \text{ A}; T_j = 25 \text{ }^\circ C$		-	4.7	-	V
		$V_{GS} = -4 \text{ V}; I_{SD} = 37.5 \text{ A}; T_j = 175 \text{ }^\circ C$		-	4.1	-	V
$t_{rr}$	reverse recovery time	$I_{SD} = 50 \text{ A}; di/dt = 500 \text{ A}/\mu s; V_{DS} = 400 \text{ V}; T_j = 25 \text{ }^\circ C$		-	45.5	-	ns
$Q_r$	recovered charge			-	250	-	nC
$I_{rrm}$	reverse recovery current			-	10	-	A



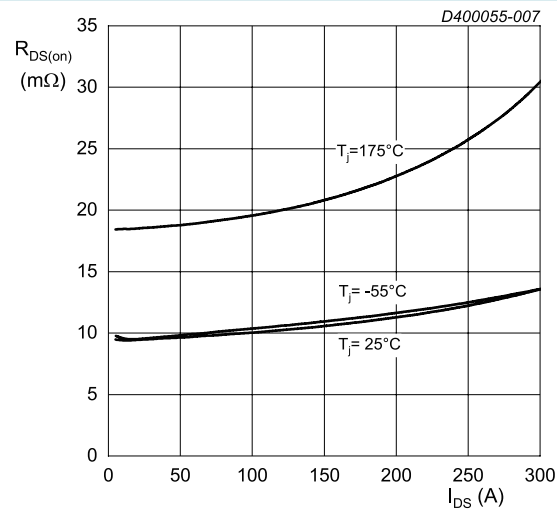
**Fig. 4. Output characteristics; drain current as a function of drain-source voltage; typical values**



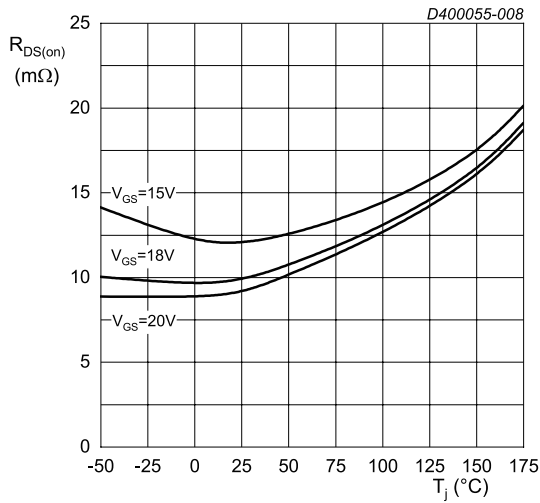
**Fig. 5. Output characteristics; drain current as a function of drain-source voltage; typical values**



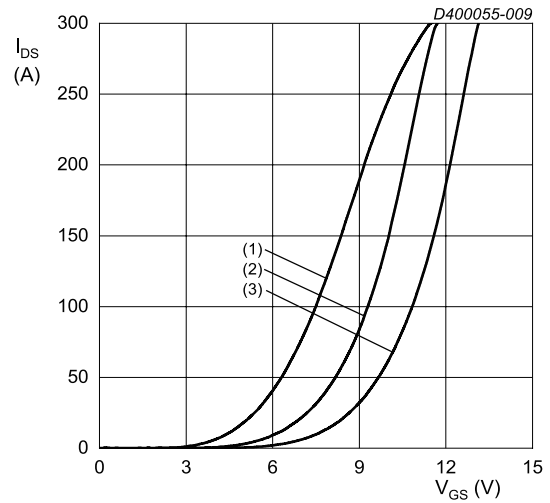
**Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values**



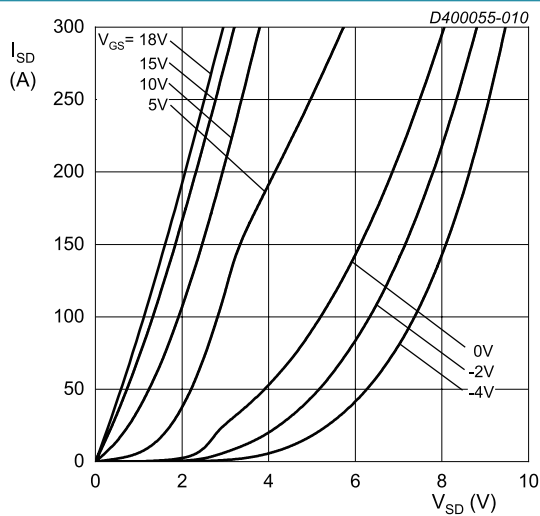
**Fig. 7. Drain-source on-state resistance as a function of drain current; typical values**



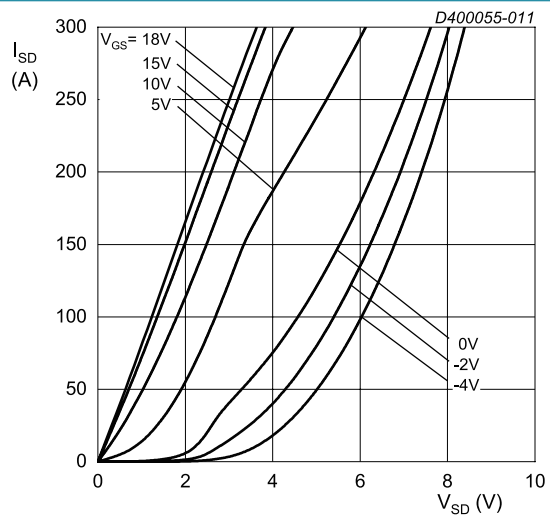
$I_{DS} = 75 \text{ A}; t_p < 200 \mu\text{s}$   
**Fig. 8. Drain-source on-state resistance as a function of junction temperature**



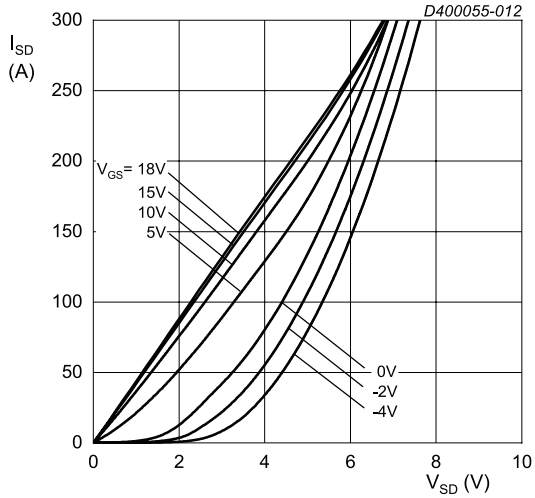
$V_{DS} = 20 \text{ V}; t_p < 200 \mu\text{s}$   
 (1)  $T_j = 175 \text{ }^\circ\text{C}$   
 (2)  $T_j = 25 \text{ }^\circ\text{C}$   
 (3)  $T_j = -55 \text{ }^\circ\text{C}$   
**Fig. 9. Transfer characteristics; drain current as a function of gate-source voltage; typical values**



$T_j = -55 \text{ }^\circ\text{C}; t_p < 200 \mu\text{s}$   
**Fig. 10. Body diode forward characteristics; typical values**

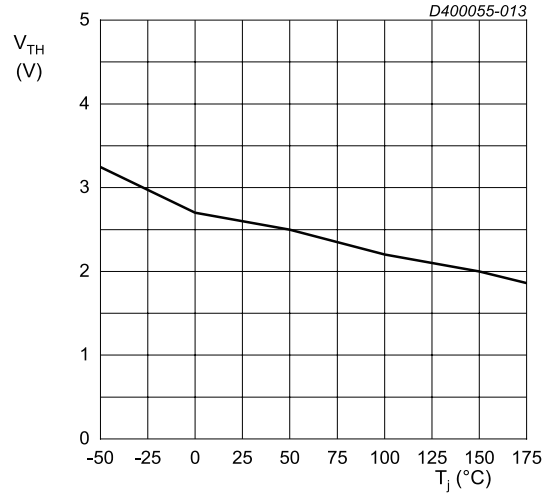


$T_j = 25 \text{ }^\circ\text{C}; t_p < 200 \mu\text{s}$   
**Fig. 11. Body diode forward characteristics; typical values**



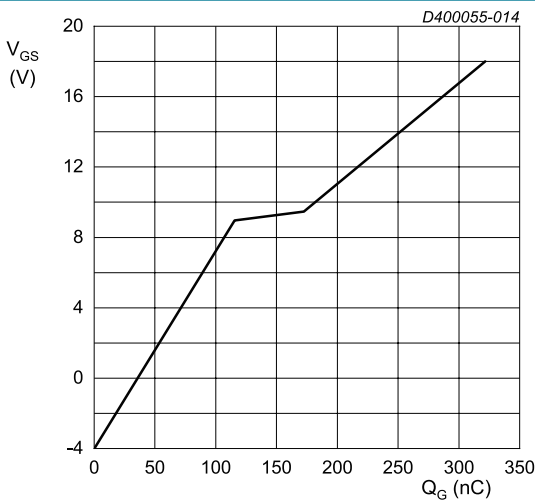
$T_j = 175\text{ }^\circ\text{C}$ ;  $t_p < 200\text{ }\mu\text{s}$

Fig. 12. Body diode forward characteristics; typical values



$V_{DS} = 10\text{ V}$ ;  $I_{DS} = 28\text{ mA}$

Fig. 13. Threshold voltage as a function of junction temperature



$I_{DS} = 75\text{ A}$ ;  $I_{GS} = 0.1\text{ mA}$ ;  $V_{DS} = 800\text{ V}$ ;  $T_j = 25\text{ }^\circ\text{C}$

Fig. 14. Gate-source voltage as a function of gate charge; typical values

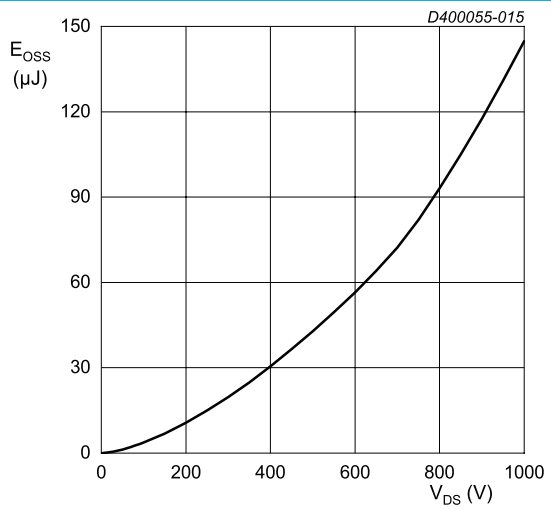
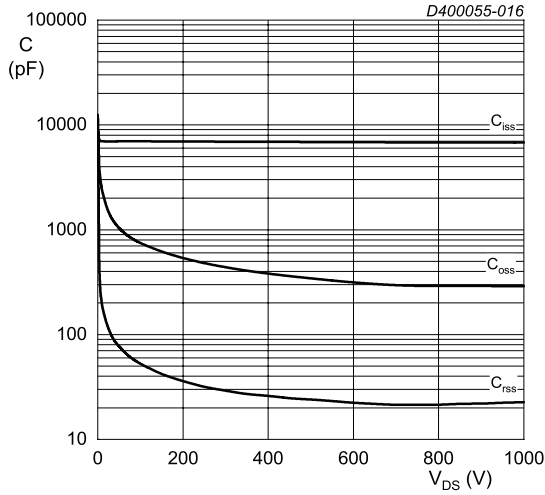


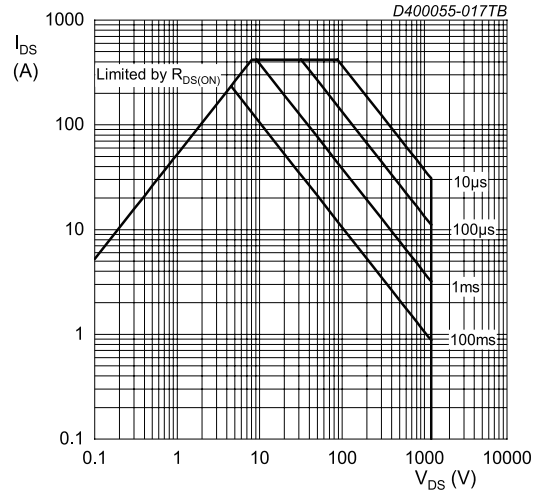
Fig. 15. Output capacitor stored energy as a function of drain-source voltage





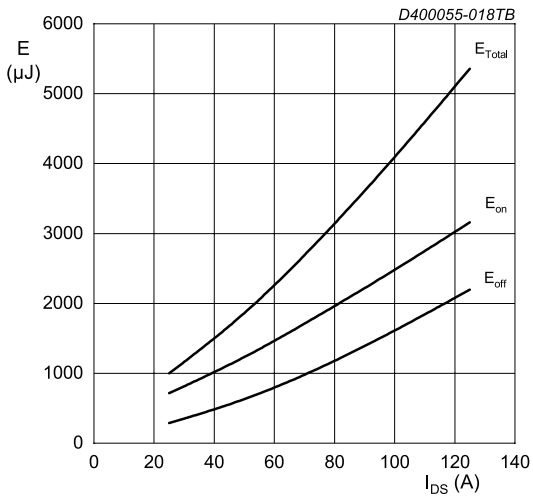
$V_{DS} = 0 - 1000\text{ V}$   
 $T_j = 25\text{ }^\circ\text{C}; V_{AC} = 25\text{ mV}; f = 1\text{ MHz}$

**Fig. 16. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values**



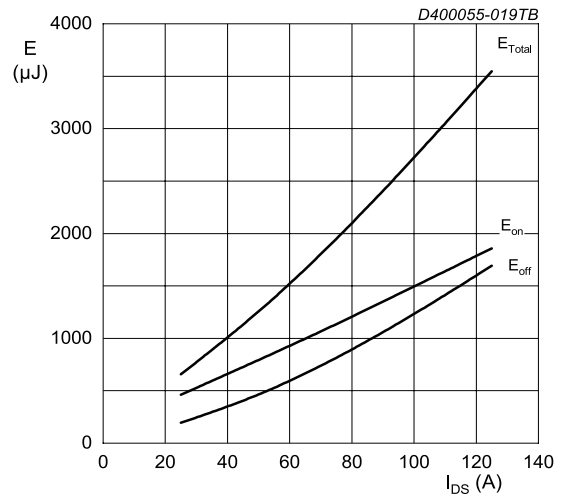
$T_j = 25\text{ }^\circ\text{C}; D = 0$   
 Parameter:  $t_p$

**Fig. 17. Forward bias safe operating area**



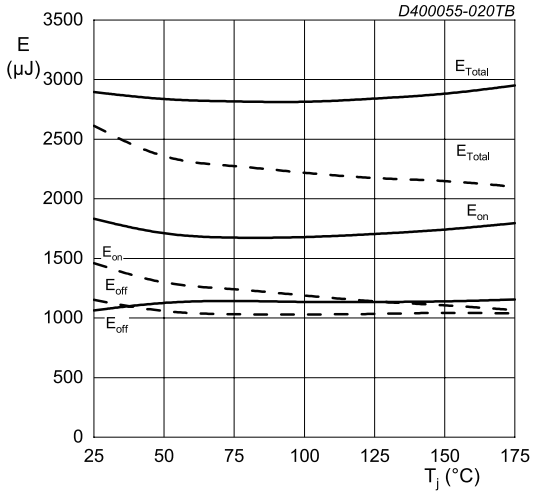
$T_j = 25\text{ }^\circ\text{C}; V_{DD} = 800\text{ V}; R_{G(ext)} = 5.1\text{ }\Omega;$   
 $V_{GS} = -4\text{ V}/18\text{ V}; L = 100\text{ }\mu\text{H}$   
 FWD = WNSC2M12120TB

**Fig. 18. Clamped Inductive Switching Energy as a function of drain current**



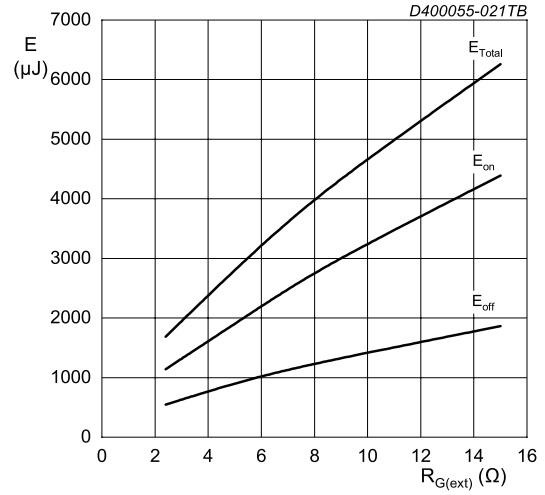
$T_j = 25\text{ }^\circ\text{C}; V_{DD} = 600\text{ V}; R_{G(ext)} = 5.1\text{ }\Omega;$   
 $V_{GS} = -4\text{ V}/18\text{ V}; L = 100\text{ }\mu\text{H}$   
 FWD = WNSC2M12120TB

**Fig. 19. Clamped Inductive Switching Energy as a function of drain current**



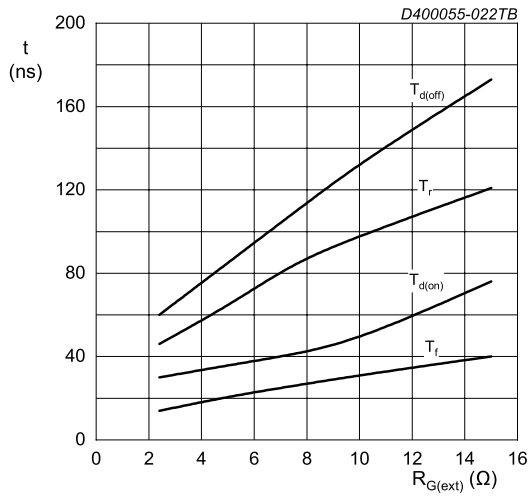
$I_{DS} = 75 \text{ A}$ ;  $V_{DD} = 800 \text{ V}$ ;  $R_{G(ext)} = 5.1 \Omega$ ;  
 $V_{GS} = -4 \text{ V}/18 \text{ V}$ ;  $L = 100 \mu\text{H}$   
 FWD = WNSC2M12120TB  
 FWD = WNSC2D401200TB(---)

Fig. 20. Clamped Inductive Switching Energy as a function of junction temperature



$T_j = 25 \text{ }^\circ\text{C}$ ;  $V_{DD} = 800 \text{ V}$ ;  $I_{DS} = 75 \text{ A}$ ;  $V_{GS} = -4 \text{ V}/18 \text{ V}$   
 FWD = WNSC2M12120TB;  $L = 100 \mu\text{H}$

Fig. 21. Clamped Inductive Switching Energy as a function of external gate resistance



$T_j = 25 \text{ }^\circ\text{C}$ ;  $V_{DD} = 800 \text{ V}$ ;  $I_{DS} = 75 \text{ A}$ ;  $V_{GS} = -4 \text{ V}/18 \text{ V}$   
 FWD = WNSC2M12120TB;  $L = 100 \mu\text{H}$

Fig. 22. Switching time as a function of external gate resistance

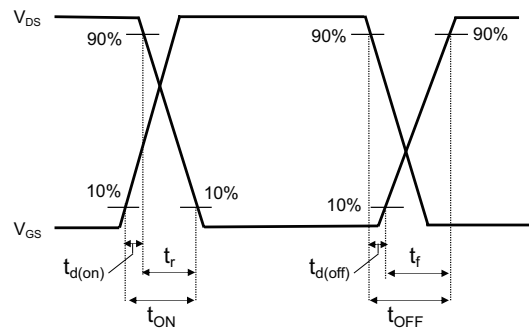
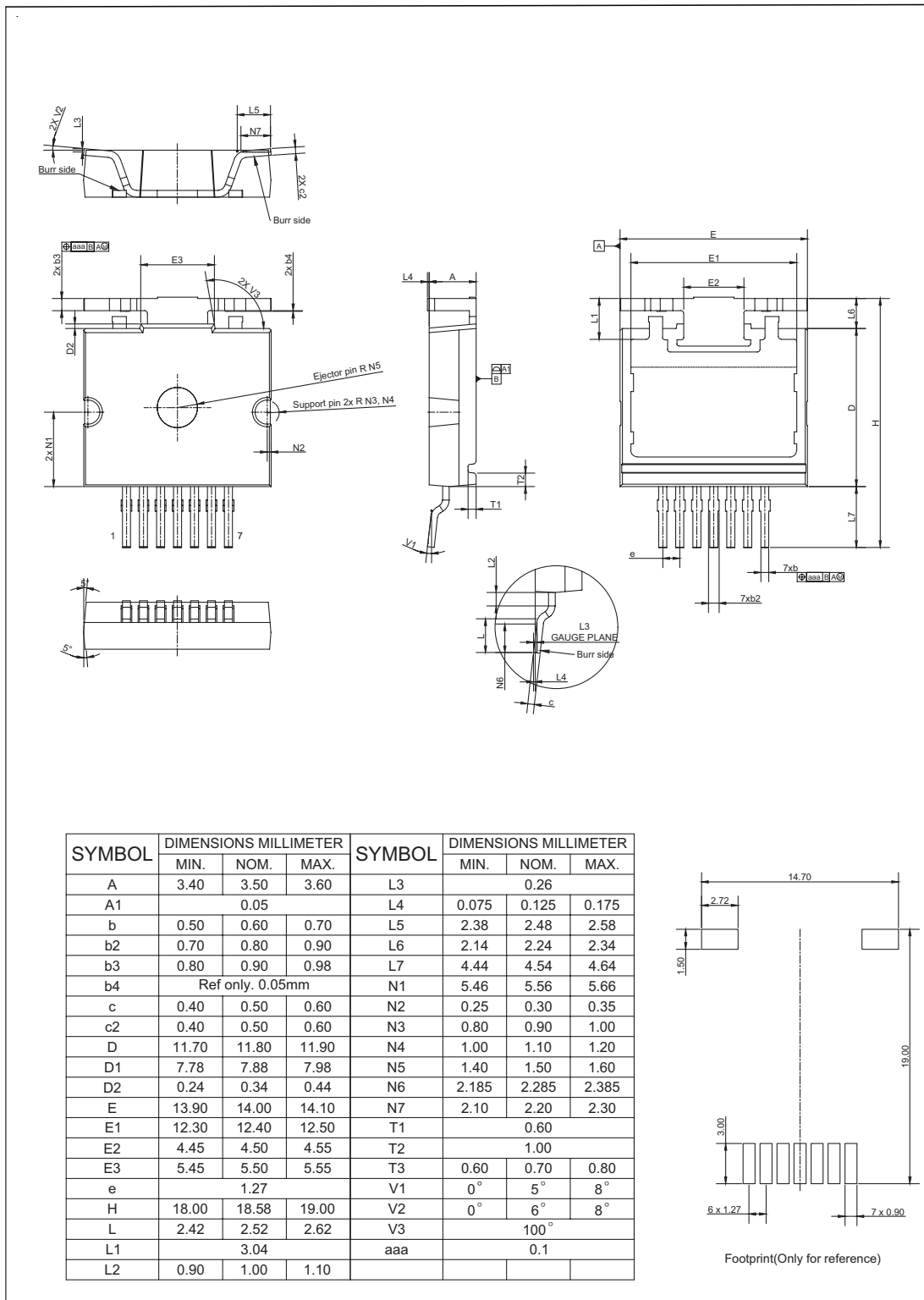


Fig. 23. Switching time definition

### 11. Package outline



## 12. Legal information

### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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